





Support & training



# **INA2128 Dual, Low-Power Instrumentation Amplifier**

# 1 Features

- Low offset voltage: 50 µV max
- Low drift: 0.5 µV/°C max
- Low input bias current: 5 nA max
- Input voltage noise: 8 nV/ $\sqrt{Hz}$  at 1 kHz •
- High bandwidth: 1.3 MHz at G=1 V/V
- High CMR: 120 dB min •
- Inputs protected to ±40 V
- Wide supply range: ±2.25 V to ±18 V
- Low quiescent current: 700 µA per channel
- ٠ Temperature range: -40°C to +85°C
- Package: 16-pin SOIC •

# 2 Applications

- Pressure transmitter
- Temperature transmitter
- Weigh scale
- Electrocardiogram (ECG)
- Analog input module
- Data acquisition (DAQ)

# **3 Description**

The INA2128 is a dual, low-power, general-purpose instrumentation amplifier (IA) offering excellent accuracy. The versatile three-op-amp design and small size make this device an excellent choice for a wide range of applications. Current-feedback input circuitry provides wide bandwidth, even at high gain (200 kHz at G = 100). A single external resistor sets any gain from 1 to 10,000. Internal input protection can withstand up to ±40 V without damage.

The INA2128 is laser-trimmed for very low offset voltage (50 µV), drift (0.5 µV/°C) and high commonmode rejection (120 dB at  $G \ge 100$ ). The device operates with power supplies as low as ±2.25 V, and quiescent current is only 700 µA per IA-a great choice for battery-operated and multiple-channel systems.

The INA2128 is available in an SOIC-16 package, and is specified from -40°C to +85°C.

Package Information

	U	
PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
INA2128	DW (SOIC, 16)	10.3 mm × 10.3 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

The package size (length × width) is a nominal value and (2)includes pins, where applicable.



**Simplified Schematic** 





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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision A (April 2007) to Revision B (May 2023)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Added the Package Information table, and the Pin Configuration and Functions, Specifications, Detailed	
	Description, Application and Implementation, Device and Documentation Support, and Mechanical,	
	Packaging, and Orderable Information sections	1
•	Added input voltage noise, high bandwidth, and temperature range bullets to <i>Features</i>	1
•	Changed <i>Features</i> bullet to show correct package name	1
•	Changed Applications bullets to show updated links	1
•	Changed Package Information table column name from BODY SIZE (NOM) to PACKAGE SIZE and add note regarding the package size.	ed 1
•	Added single supply specification to Absolute Maximum Ratings	
•	Added note clarifying output short-circuit to ground in <i>Absolute Maximum Ratings</i> refers to short-circuit to VS / 2	o 5
•	Added single supply specification to Recommended Operating Conditions	
•	Changed input common-mode voltage range specification from V – 2 to (V–) + 2 in <i>Recommended Oper</i> Conditions	rating
•	Deleted INA128-HT and INA129-HT operating temperature specifications from <i>Recommended Operating</i>	g
	Added specified temperature range to Recommended Operating Conditions	5 5
	Added test conditions below Electrical Characteristics title	5 6
	Changed test condition for offset voltage drift specification in <i>Electrical Characteristics</i> from "TA - TMIN"	0 to
	TMAX" to "TA = $-40^{\circ}$ C to $+85^{\circ}$ C" for clarity	6
	Changed "+0.5+0/G" to "+0.5+20/G" in MAX column of Offset voltage RTL vs temperature row of <i>Electric</i> .	0 al
	Characteristics	6
•	Changed typical long-term stability specification from ±0.1±3/GµV/mo to ±0.2±3/GµV/mo in <i>Electrical</i>	6
•	Deleted typical specification and changed common-mode voltage specification from $(V_{-}) + 2 V$ minimum	and
	(V+) = 2 V maximum across one row in Electrical Characteristics	6 היי ויי 1
•	Deleted typical VCM specifications in <i>Electrical Characteristics</i>	0 6
•	Added test condition of "RS = 0.0" to safe input voltage specification in <i>Electrical Characteristics</i> for clar	itv
		6
•	Changed parameter name to Input bias current and added test condition "TA = $-40^{\circ}$ C to $+85^{\circ}$ C" to input	bias
	current drift specification in <i>Electrical Characteristics</i> for clarity	
•	Changed parameter name to Input offset current drift and added test condition "TA = $-40^{\circ}$ C to $+85^{\circ}$ C" to	input
	offset current drift specification in <i>Electrical Characteristics</i> for clarity	
•	Changed maximum gain error specification for INA128PA/UA and INA129PA/UA with G = 1 from ±0.01%	6 to
	±0.1% in Electrical Characteristics	6

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•	Changed parameter name to Gain drift and added test condition "TA = -40°C to +85°C" for gain drift in <i>Electrical Characteristics</i> for clarity	6
•	Changed parameter names from "Voltage - Positive" to "Positive output voltage swing" and from "Voltage - Negative" to "Negative output voltage swing" in <i>Electrical Characteristics</i>	6
•	Deleted typical positive and negative output voltage swing specifications in <i>Electrical Characteristics</i>	6
•	Added test condition "Continuous to VS / 2" short-circuit current specification in <i>Electrical Characteristics</i>	
	for clarity	6
•	Changed typical bandwidth specification for $G = 10$ from 700 kHz to 600 kHz in <i>Electrical Characteristics</i>	6
•	Changed typical slew rate specification from 4 V/us to 1.2 V/us in <i>Electrical Characteristics</i>	6
	Changed typical settling time specification for $G = 1$ , $G = 10$ , from 7 us to 9 us in <i>Electrical Characteristics</i>	
	= 1, 0 = 10, 10117 + 1000 + 100000 + 100000 + 100000 + 100000 + 100000 + 100000 + 100000 + 100000 + 10000000 + 1000000 + 100000 + 100000 + 100000000	6
•	Deleted parameter "Temperature Range" as made redundant by "Recommended Operating Conditions" and	nd
	"Absolute Maximum Ratings"	6
•	Changed parameter name to "Total quiescent current" and deleted redundant voltage range operating	
	temperature range, and specification temperature range specifications from Electrical Characteristics	6
	Added test conditions below the Typical Characteristics title	0
	Changed Figure 6.1. Cain us Frequency	0
	Changed Figure 6-1, Gain vs Frequency	0
	Changed Figure 6-5, Positive Power Supply Rejection vs Frequency	0
	Changed Figure 6-4, Negative Power Supply Rejection vs Frequency	0
•	Changed Figure 6-7, Crosstark VS Frequency	8
•	Changed Figure 6-8, Input-Referred Voltage Noise Vs Frequency	8
•	Changed Figure 6-9, Settling Time vs Gain	8
•	Changed Figure 6-11, Input Overvoltage V/I Characteristics	8
•	Changed Figure 6-12, Offset Voltage Warm-Up	8
•	Changed Output Voltage Swing vs Output Current, into two separate plots, one for positive (Figure 6-14) a	nd
	one for negative (Figure 6-15)	8
•	Changed Figure 6-22 to Figure 6-24, Large-Signal Step Response	8



# **5** Pin Configuration and Functions



Figure 5-1. DW Package, 16-Pin SOIC (Top View)



## **6** Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	IAX	UNIT
V	Supply voltage	Dual supply, $V_S = (V+) - (V-)$		±18	V
VS	Supply voltage	Single supply, $V_S = (V+) - 0 V$		36	v
	Analog input voltage			±40	V
	Output short-circuit <sup>(2)</sup>		Continuous		
T <sub>A</sub>	Operating temperature		-40	125	°C
	Junction temperature			150	°C
	Lead temperature (soldering, 10 s)			300	°C
T <sub>stg</sub>	g Storage temperature		-55	125	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Short-circuit to  $V_S / 2$ .

## 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±50	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	TYP	MAX	UNIT
Vs	Supply voltage	Single-supply	4.5	30	36	V
		Dual-supply	±2.25	±15	±18	v
	Input common-mode voltage range for	V <sub>O</sub> = 0 V	(V–) + 2		(V+) – 2	V
T <sub>A</sub>	Specified temperature		-40		85	°C

#### 6.4 Thermal Information

		INA		
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	P (PDIP)	UNIT
		8 PINS	8 PINS	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	110	46.1	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	57	34.1	°C/W
R <sub>0JB</sub>	Junction-to-board thermal resistance	54	23.4	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	11	11.3	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	53	23.2	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



## 6.5 Electrical Characteristics

at  $T_A = 25^{\circ}$ C,  $V_S = \pm 15$  V,  $R_L = 10$  k $\Omega$ ,  $V_{REF} = 0$  V,  $V_{CM} = V_S$  / 2, and G = 1 (unless otherwise noted)

	PARAMETER	TES	MIN	TYP	МАХ	UNIT			
INPUT		·			·				
V		INA2128U				±10 ±100 / G	±50 ±500 / G		
Vos	Oliset voltage (RTT)	INA2128UA				±25 ±100 / G	±125 ±1000 / G	μv	
		INA2128U				±0.2 ±2 / G	±0.5 ±20 / G		
	Offset voltage drift (RTI)	$I_A = -40^{\circ}$ C to +85° C	INA2128U	A		±0.2 ±5 / G	±1 ±20 / G	μv/°C	
	Power-supply rejection		INA2128U			±0.2 ±20 / G	±1 ±100 / G		
PORK	ratio (RTI)	$V_{\rm S} = \pm 2.25  \text{V}  10 \pm 10  \text{V}$	INA2128U	A		±0.2 ±20 / G	±2 ±200 / G	μν/ν	
	Long-term stability		•			±0.2 ±3 / G		μV/mo	
	Inputimpodonoo	Differential				10    2			
		Common-mode				100    9		Gtz II br	
V <sub>CM</sub>	Common-mode voltage <sup>(1)</sup>	V <sub>O</sub> = 0 V			(V–) + 2		(V+) – 2	V	
	Safe input voltage	R <sub>S</sub> = 0 Ω					±40	V	
	RR Common-mode rejection ratio			0.1	INA2128U	80	86		
			6 = 1	INA2128UA	73	86			
			0 - 10	INA2128U	100	106		dB	
CMPP			G = 10	INA2128UA	93	106			
CIVIRR		$\Delta R_{\rm S} = 1  \text{K}\Omega,  V_{\rm CM} = \pm 13  \text{V}$	G = 100	INA2128U	120	125			
			G = 100	INA2128UA	110	125			
			G = 1000	INA2128U	120	130			
			INA2128UA		110	130			
INPUT E	BIAS CURRENT								
1-	Input bias current	INA2128U				±2	±5	۳Å	
IB	Input bias current	INA2128UA				±2	±10	IIA	
	Input bias current drift	$T_A = -40^{\circ}C$ to $+85^{\circ}C$				±30		pA/°C	
laa	Input offset current	INA2128U				±1	±5	nΔ	
105	input onset current	INA2128UA				±1	±10	ПА	
	Input offset current drift	$T_A = -40^{\circ}C$ to +85°C				±30		pA/°C	
NOISE									
			f = 10 Hz			10			
	Voltage poise (RTI)	$G = 1000 B_0 = 0.0$	f = 100 Hz			8		nV/√Hz	
		0 - 1000, NS - 0 12	f = 1 kHz			8			
			f <sub>B</sub> = 0.1 Hz	to 10 Hz		0.2		μV <sub>PP</sub>	
		f = 10 Hz				0.9		nA/√ <del>Hz</del>	
	Current noise	f = 1 kHz				0.3		Pr. 9.11.16	
		f <sub>B</sub> = 0.1 Hz to 10 Hz				30		рА <sub>РР</sub>	



#### 6.5 Electrical Characteristics (continued)

at T<sub>A</sub> = 25°C, V<sub>S</sub> = ±15 V, R<sub>L</sub> = 10 k $\Omega$ , V<sub>REF</sub> = 0 V, V<sub>CM</sub> = V<sub>S</sub> / 2, and G = 1 (unless otherwise noted)

	PARAMETER	TE	EST CONDITIONS	MIN	ТҮР	MAX	UNIT		
GAIN				·					
	Gain equation				1 + (50 kΩ / R <sub>G</sub> )		V/V		
G	Gain			1		10000	V/V		
		0 - 1	INA2128U		±0.01	±0.024			
		6 = 1	INA2128UA		±0.01	±0.1	1		
		C = 10	INA2128U		±0.02	±0.4			
CE	Coin orror	G = 10	INA2128UA		±0.02	±0.5	0/		
GE	Gain enor	C = 100	INA2128U		±0.05	±0.5	70		
		G = 100	INA2128UA		±0.05	±0.7			
		C = 1000	INA2128U		±0.5	±1			
		G = 1000	INA2128UA		±0.5	±2			
	Coin drift <sup>(2)</sup>	$T = 40^{\circ}C + 25^{\circ}C$			±1	±10	nnm/°C		
	Gain unit	T <sub>A</sub> = -40 C to +65 C	50-kΩ or 49.4-kΩ resistance <sup>(3)</sup>		±25	±100			
		$C = 1 V_{1} = \pm 12 G V_{1}$	INA2128U		±0.0001	±0.001			
	Gain nonlinearity	G = 1, V <sub>O</sub> = ±13.0 V	INA2128UA		±0.0001	±0.002			
		0 - 10	INA2128U		±0.0003	±0.002	1		
		G = 10	INA2128UA		±0.0003	±0.004	% of FSR		
		0 - 100	INA2128U		±0.0005	±0.002			
		G = 100	INA2128UA		±0.0005	±0.004			
		G = 1000 <sup>(4)</sup>			±0.001		1		
Ουτρυ	т			·					
	Positive output voltage			(V+) – 1.4			V		
	Negative output voltage			(V–) + 1.4			V		
CL	Load capacitance	Stable operation			1000		pF		
I <sub>SC</sub>	Short-circuit current	Continuous to $V_S$ / 2			+6/-15		mA		
FREQU	ENCY RESPONSE			·					
		G = 1			1.3		MHz		
DW	Pondwidth 2 dP	G = 10			600				
DVV	Bandwidth, -3 dB	G = 100			200		kHz		
		G = 1000			20				
SR	Slew rate	G = 10, V <sub>O</sub> = ±10 V			1.2		V/µs		
			G = 1		9				
	Cattling time	To 0.019/	G = 10		9		µs		
I'S	Setting time	10 0.01 %	G = 100		12				
			G = 1000		80				
	Overload recovery	50% input overload			4		μs		
POWER	R SUPPLY								
lq	Total quiescent current	V <sub>IN</sub> = 0 V			±1.4	±1.5	mA		

(1) Input common-mode voltage varies with output voltage; see Typical Characteristics.

Specified by wafer test. (2)

Temperature coefficient of the 50-k $\Omega$  or 49.4-k $\Omega$  term in the gain equation.

(3) (4) Nonlinearity measurements in G = 1000 are dominated by noise. Typical nonlinearity is ±0.001%.



### **6.6 Typical Characteristics**





















# 7 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 7.1 Application Information

Figure 7-1 shows the basic connections required for operation of the INA2128. Applications with noisy or high impedance power supplies may require decoupling capacitors close to the device pins as shown.

The output is referred to the output reference (Ref) terminals (Ref<sub>A</sub> and Ref<sub>B</sub>) which are normally grounded. These must be low-impedance connections to assure good common-mode rejection. A resistance of 8  $\Omega$  in series with a Ref pin will cause a typical device to degrade to approximately 80 dB CMR (G = 1).

The INA2128 has separate output sense feedback connections,  $Sense_A$  and  $Sense_B$ . These must be connected to their respective output terminals for proper operation. The output sense connection can be used to sense the output voltage directly at the load for best accuracy.

#### 7.2 Typical Application



Figure 7-1. Basic Connections



### 7.2.1 Setting The Gain

Gain of the INA2128 is set by connecting a single external resistor, RG, connected as shown:

$$G = 1 + \frac{50k\Omega}{R_G}$$
(1)

Commonly-used gains and resistor values are shown in Figure 7-1.

The 50 k $\Omega$  term in Equation 1 comes from the sum of the two internal feedback resistors, A<sub>1</sub> and A<sub>2</sub>. These on-chip metal film resistors are laser-trimmed to accurate absolute values. The accuracy and temperature coefficient of these resistors are included in the gain accuracy and drift specifications of the INA2128.

The stability and temperature drift of the external gain setting resistor, RG, also affects gain. RG's contribution to gain accuracy and drift can be directly inferred from the gain equation (1). Low resistor values required for high gain can make wiring resistance important. Sockets add to the wiring resistance which will contribute additional gain error in gains of approximately 100 or greater.

#### 7.2.2 Dynamic Performance

The typical performance curve Figure 6-1 shows that despite its low quiescent current, the INA2128 achieves wide bandwidth, even at high gain. This is due to its current feedback topology. Settling time also remains excellent at high gain—see Figure 6-9.

#### 7.2.3 Noise Performance

The INA2128 provides very low noise in most applications. Low frequency noise is approximately 0.2  $\mu V_{pp}$  measured from 0.1 Hz to 10 Hz (G ≥ 100). This provides dramatically improved noise when compared to state-of-the-art chopper-stabilized amplifiers.

#### 7.2.4 Offset Trimming

The INA2128 is laser-trimmed for low offset voltage and offset voltage drift. Most applications require no external offset adjustment. Figure 7-2 shows an optional circuit for trimming the output offset voltage. The voltage applied to Ref terminal is summed with the output. The op amp buffer provides low impedance at the Ref terminal to preserve good common-mode rejection.



Figure 7-2. Optional Trimming of Output Offset Voltage



#### 7.2.5 Input Bias Current Return Path

The input impedance of the INA2128 is extremely high—approximately  $10^{10} \Omega$ . However, a path must be provided for the input bias current of both inputs. This input bias current is approximately ±2 nA. High input impedance means that this input bias current changes very little with varying input voltage.

Input circuitry must provide a path for this input bias current for proper operation. Figure 7-3 shows various provisions for an input bias current path. Without a bias current path, the inputs float to a potential that exceeds the common-mode range of the INA2128 and the input amplifiers saturate.

If the differential source resistance is low, the bias current return path can be connected to one input (see the thermocouple example in Figure 7-3). With higher source impedance, using two equal resistors provides a balanced input with possible advantages of lower input offset voltage due to bias current and better high-frequency common-mode rejection.

#### 7.2.6 Input Common-Mode Range

The linear input voltage range of the input circuitry of the INA2128 is from approximately 1.4 V less than the positive supply voltage to 1.7 V greater than the negative supply. As a differential input voltage causes the output voltage increase, the linear input range is limited by the output voltage swing of amplifiers  $A_1$  and  $A_2$ . Therefore, the linear common-mode input range is related to the output voltage of the complete amplifier. This behavior also depends on supply voltage—see performance curves Figure 6-6 and Figure 6-5.

Input-overload can produce an output voltage that appears normal. For example, if an input overload condition drives both input amplifiers to the positive output swing limit, the difference voltage measured by the output amplifier is near zero. The output of the INA2128 is near 0 V even though both inputs are overloaded.



Figure 7-3. Providing an Input Common-Mode Current Path



#### 7.2.7 Low-Voltage Operation

The INA2128 can be operated on power supplies as low as  $\pm 2.25$  V. Performance remains excellent with power supplies ranging from  $\pm 2.25$  V to  $\pm 18$  V. Most parameters vary only slightly throughout this supply voltage range—see Section 6.6. Operation at very low supply voltage requires careful attention to make sure that the input voltages remain within the linear range. Voltage swing requirements of internal nodes limit the input common-mode range with low power-supply voltage. Typical performance curves, Figure 6-5 and Figure 6-6, show the range of linear operation for  $\pm 15$ -V,  $\pm 5$ -V, and  $\pm 2.5$ -V supplies.

#### 7.2.8 Input Protection

The inputs of the INA2128 are individually protected for voltages up to  $\pm 40$  V. For example, a condition of -40 V on one input and  $\pm 40$  V on the other input will not cause damage. Internal circuitry on each input provides low series impedance under normal signal conditions. To provide equivalent protection, series input resistors would contribute excessive noise. If the input is overloaded, the protection circuitry limits the input current to a safe value of approximately 1.5 mA to 5 mA. The typical performance curve "Input Bias Current vs Common-Mode Input Voltage" shows this input current limit behavior. The inputs are protected even if the power supplies are disconnected or turned off.



Figure 7-4. Two-Axis Bridge Amplifier



#### 7.2.9 Channel Crosstalk

The two channels of the INA2128 are completely independent, including all bias circuitry. At dc and low frequency, there is virtually no signal coupling between channels. Crosstalk increases with frequency and depends on circuit gain, source impedance, and signal characteristics.

As source impedance increases, careful circuit layout helps achieve lowest channel crosstalk. Most crossstalk is produced by capacitive coupling of signals from one channel to the input section of the other channel. To minimize coupling, separate the input traces as far as practical from any signals associated with the opposite channel. A grounded guard trace surrounding the inputs helps reduce stray coupling between channels. Run the differential inputs of each channel parallel to each other or directly adjacent on top and bottom side of a circuit board. Stray coupling then tends to produce a common-mode signal which is rejected by the IA input.



Figure 7-5. Sum of Differences Amplifier



Figure 7-6. ECG Amplifier With Right-Leg Drive



## 8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### 8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 8.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 8.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

#### 8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 8.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

## 9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
INA2128U	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA2128U	Samples
INA2128U/1K	ACTIVE	SOIC	DW	16	1000	RoHS & Green	Call TI	Level-3-260C-168 HR		INA2128U	Samples
INA2128UA	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR		INA2128U A	Samples
INA2128UA/1K	ACTIVE	SOIC	DW	16	1000	RoHS & Green	Call TI	Level-3-260C-168 HR		INA2128U A	Samples
INA2128UG4	LIFEBUY	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA2128U	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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# PACKAGE OPTION ADDENDUM

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## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA2128U/1K	SOIC	DW	16	1000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
INA2128UA/1K	SOIC	DW	16	1000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1



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# PACKAGE MATERIALS INFORMATION

14-Mar-2023



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA2128U/1K	SOIC	DW	16	1000	356.0	356.0	35.0
INA2128UA/1K	SOIC	DW	16	1000	356.0	356.0	35.0

# TEXAS INSTRUMENTS

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# TUBE



# - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
INA2128U	DW	SOIC	16	40	507	12.83	5080	6.6
INA2128UA	DW	SOIC	16	40	507	12.83	5080	6.6
INA2128UG4	DW	SOIC	16	40	507	12.83	5080	6.6

# **DW 16**

# **GENERIC PACKAGE VIEW**

# SOIC - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

7.5 x 10.3, 1.27 mm pitch

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





# **DW0016A**



# **PACKAGE OUTLINE**

SOIC - 2.65 mm max height

SOIC



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



# DW0016A

# **EXAMPLE BOARD LAYOUT**

# SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DW0016A

# **EXAMPLE STENCIL DESIGN**

# SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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